

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

Claims 1-20 (canceled)

Claim 21 (New): A method of validating an electronic component, said method comprising:
 providing said electronic component;
 making a temporary electrical connection with said electronic component using a contact structure comprising palladium; and
 exercising said electronic component.

Claim 22 (New): The method of claim 21, wherein said exercising said electronic component comprises burning in said electronic component.

Claim 23 (New): The method of claim 22, wherein said contact structure comprises a palladium cobalt alloy.

Claim 24 (New): The method of claim 21, wherein said exercising said electronic component comprises testing said electronic component.

Claim 25 (New): The method of claim 24, wherein said contact structure comprises a palladium cobalt alloy.

Claim 26 (New): A contact structure comprising:
 a base secured to a substrate; and
 a body disposed at least in part away from said substrate, wherein said body is attached to said base and comprises palladium.

Claim 27 (New): The contact structure of claim 26, wherein said body comprises a palladium cobalt alloy.

Claim 28 (New): The contact structure of claim 26, wherein said body comprises a palladium rhodium alloy.

Claim 29 (New): The contact structure of claim 26, wherein said body comprises a palladium tungsten alloy.

Claim 30 (New): The contact structure of claim 26, wherein said body comprises a tip.

Claim 31 (New): The contact structure of claim 30, wherein said tip comprises palladium.

Claim 32 (New): The contact structure of claim 30, wherein said tip comprises a palladium cobalt alloy.

Claim 33 (New): The contact structure of claim 30, wherein said tip is integrally formed with said body.

Claim 34 (New): The contact structure of claim 26, wherein a majority of said body comprises palladium.

Claim 35 (New): The contact structure of claim 26, wherein said base and said body are integrally formed.

Claim 36 (New): The contact structure of claim 26, wherein said body comprises a beam that is structurally distinct from said base.

Claim 37 (New): The contact structure of claim 26, wherein said contact structure is resilient.

Claim 38 (New): The contact structure of claim 26, wherein said beam comprises a plurality of layers of material, wherein at least one of said layers comprises palladium.

Claim 39 (New): The contact structure of claim 26, wherein said base is attached to a semiconductor die.

Claim 40 (New): The contact structure of claim 39, wherein said semiconductor device is resident on a semiconductor wafer.

Claim 41 (New): The contact structure of claim 26, wherein said base is attached to a probe card assembly.

Claim 42 (New): A contact structure comprising:
a substrate; and
probing means for an electronic device, said probing means secured to said substrate and comprising palladium.

Claim 43 (New): The contact structure of claim 42, wherein said probing means comprises a palladium cobalt alloy.

Claim 44 (New): The contact structure of claim 43, wherein said electronic device is a semiconductor die.

Claim 45 (New): The contact structure of claim 43, wherein said electronic device is an unsingulated semiconductor wafer.

Claim 46 (New): The contact structure of claim 42, wherein said substrate comprises a semiconductor die.

Claim 47 (New): The contact structure of claim 46, wherein said semiconductor die is resident on a semiconductor wafer.

Claim 48 (New): The contact structure of claim 42, wherein said substrate composes a probe card assembly.

Claim 49 (New): An interconnect structure for interconnecting first and second electronic components, said interconnect structure comprising palladium.

Claim 50 (New): The interconnect structure of claim 49, wherein said interconnect structure comprises a palladium cobalt alloy.

Claim 51 (New): The interconnect structure of claim 49, wherein said interconnect structure comprises a palladium rhodium alloy.

Claim 52 (New): The interconnect structure of claim 49, wherein said interconnect structure comprises a palladium tungsten alloy.

Claim 53 (New): The interconnect structure of claim 49, wherein said interconnect structure comprises a tip, and said tip comprises palladium.

Claim 54 (New): The interconnect structure of claim 53, wherein said tip comprises a palladium cobalt alloy.

Claim 55 (New): The interconnect structure of claim 49, wherein a majority of said interconnect structure comprises palladium.

Claim 56. (New) The interconnect structure of claim 49, wherein said interconnect structure comprises:

- a first portion secured to said first electronic component; and
- a second portion for contacting said second electronic component.

Claim 57. (New) The interconnect structure of claim 56, wherein said first portion comprises a post and said second portion comprises a tip, said interconnect structure further comprising a beam to which said post and said tip are attached.

Claim 58 (New): The interconnect structure of claim 57, wherein said beam is cantilevered.

Claim 59 (New): The interconnect structure of claim 49, wherein said interconnect structure is resilient.

Claim 60 (New): The interconnect structure of claim 49, wherein said interconnect structure comprises a plurality of layers of material, wherein at least one of said layers comprises palladium.

Claim 61 (New): The interconnect structure of claim 49, wherein said interconnect structure is attached to said first electronic component and said first electronic component is a semiconductor die.

Claim 62 (New): The interconnect structure of claim 61, wherein said semiconductor device is resident on a semiconductor wafer.

Claim 63 (New): The interconnect structure of claim 49, wherein said interconnect structure is attached to said first electronic component and said first electronic component is a probe card assembly.

Claim 64 (New): The interconnect structure of claim 63, wherein said second electronic device is a semiconductor die.

Claim 65 (New): The interconnect structure of claim 64, wherein said semiconductor die is resident on a semiconductor wafer.